



## F2N60

## N-沟道功率 MOS 管/N-CHANNEL POWER MOSFET

◆应用:电子镇流器 电子变压器 开关电源

◇Applications:Electronic Ballast Electronic Transformer Switch Mode Power Supply

◆特点:热阻低 开关速度快 输入阻抗高 符合 RoHS 规范

◇Features:Low Thermal Resistance High Speed Switching High Input Resistance  
RoHS Compliant

◆最大额定值 (T<sub>c</sub>=25°C)

◇Absolute Maximum Ratings (T<sub>c</sub>=25°C)

参数 Parameter	符号 Symbol	额定值 Value	单位 Unit
漏-源电压 Drain-Source Voltage	V <sub>DS</sub>	600	V
栅-源电压 Gate-Source Voltage	V <sub>GS</sub>	±20	V
漏极电流 Continuous Drain Current	I <sub>D</sub>	T <sub>c</sub> =25°C	2.4
		T <sub>c</sub> =100°C	1.5
耗散功率 Power Dissipation	P <sub>D</sub>	64	W
最高结温 Junction Temperature	T <sub>j</sub>	150	°C
贮存温度 Storage Temperature	T <sub>stg</sub>	-55~150	°C

◆电特性 (T<sub>c</sub>=25°C)

◇Electronic Characteristics (T<sub>c</sub>=25°C)

参数名称 Characteristics	符号 Symbol	测试条件 Test Condition	数值 Numerical Value		单位 Unit
			最小值 Min	最大值 Max	
漏-源击穿电压 Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0, I <sub>D</sub> =250 μA	600		V
栅极开启电压 Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250 μA	2	4	V
漏-源漏电流 Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =Rated BV <sub>DSS</sub> V <sub>GS</sub> =0		100	μA
		V <sub>DS</sub> =0.8Rated BV <sub>DSS</sub> V <sub>GS</sub> =0, T <sub>j</sub> =125°C		250	
通态漏极电流 On State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> >I <sub>D(ON)</sub> ×R <sub>DS(on)MAX</sub> V <sub>GS</sub> =10V	2.4		A
栅极漏电流 Gate-Body Leakage Current (V <sub>DS</sub> =0)	I <sub>GSS</sub>	V <sub>GS</sub> =±20		±100	nA
漏-源导通电阻 Static Drain-Source On Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1.2A		4.7	Ω
热阻结-壳 Thermal Resistance Junction-Case	R <sub>θJc</sub>			2	°C/W

